FM30P80K/X

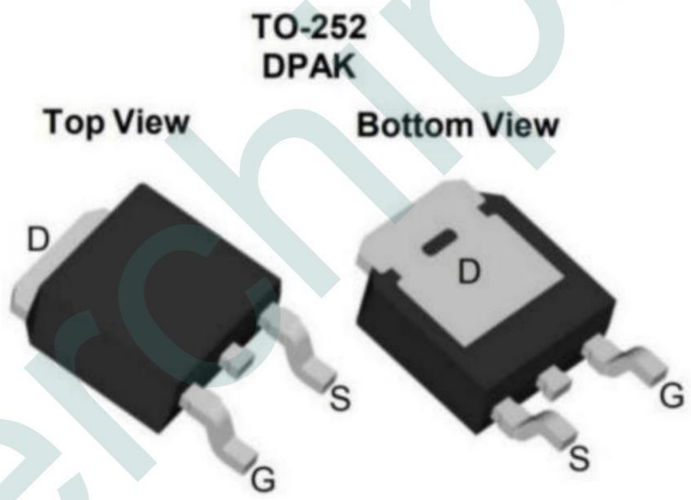
P-Channel Trench Power MOSFET

- -30V, -80A
- RDS(ON)=6.9mΩ @VGS =10V
- RDS(ON)=9.9mΩ @ VGS=4.5V
- Fast Switching
- Advanced Trench Technology
- Provide Excellent RDS(ON) and Low Gate Charge
- 100% UIS Tested

Application

- LCD TV
- Notebook
- Elevator
- Inductive heating
- Power tools

Package



Absolute Maximum Ratings (T_C=25℃unless otherwise specified)

Parameter		Symbol	Value	Units
Drain-Source Voltage		V_{DSS}	-30	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current	（Tc=25℃）	I_D	-80	A
	（Tc=100℃）		-50	A
Pulsed Drain Current NOTE1		I_{DM}	-250	A
Single Pulse Avalanche Energy NOTE2		E_{AS}	225	mJ
Power Dissipation	(Tc=25℃)	P_D	52	W
Thermal Resistance Junction-to-Case		$R_{\theta JC}$	2.3	℃/W
Operating and Storage Temperature Range		T_J , T_{STG}	-55 to +150	℃

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